

Figure 1

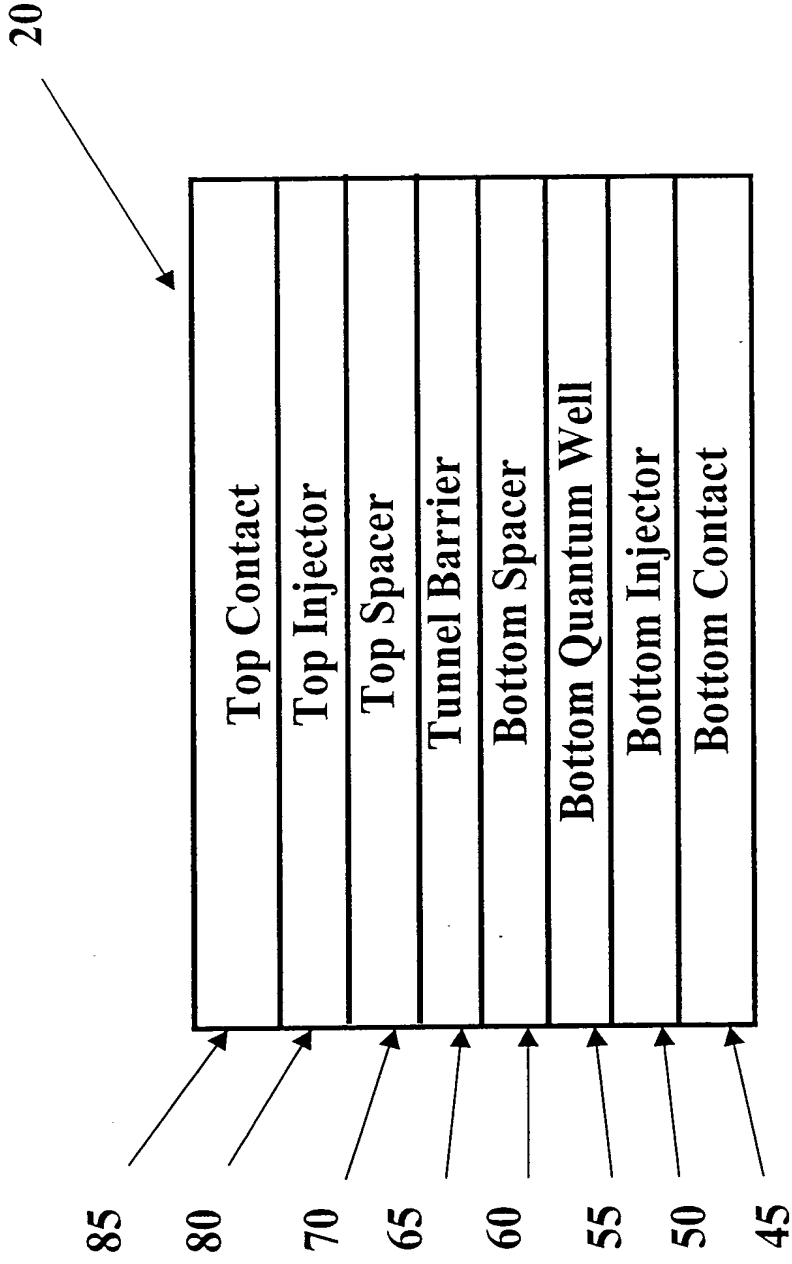


Figure 2

30

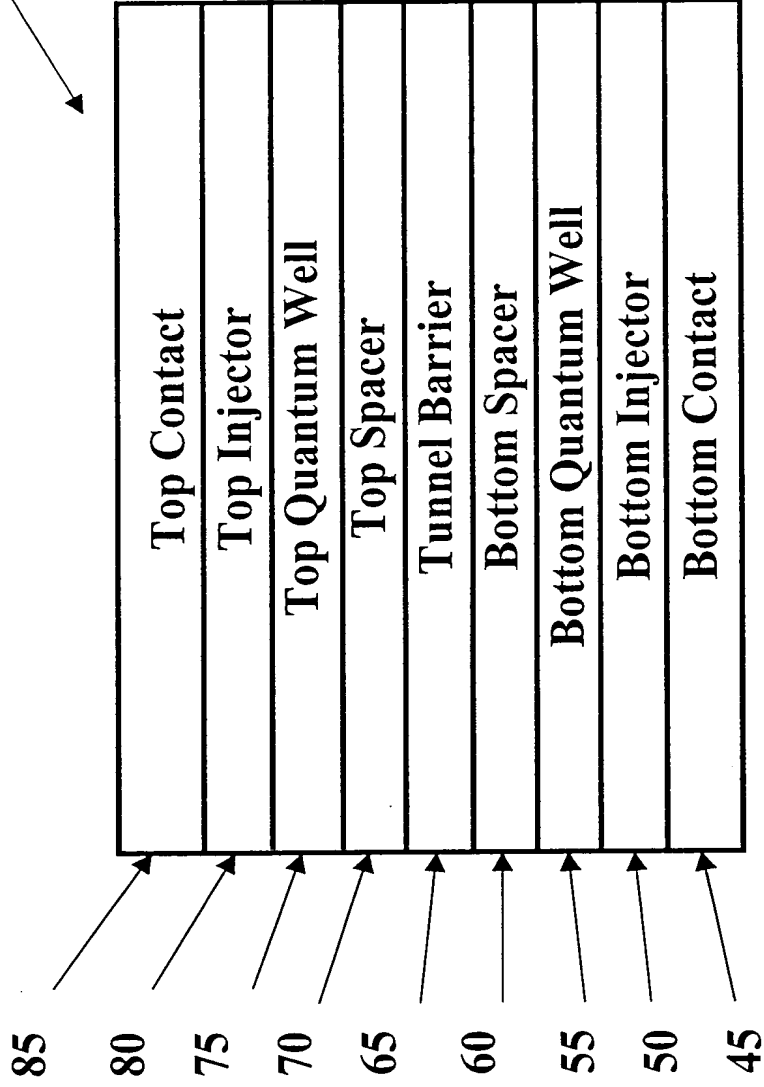


Figure 3

~50 nm n+ Si
20 nm n++ Si
4 nm undoped Si
5 nm p+Si/Si _{0.5} Ge _{0.5} DG-SL 5 periods
B δ-doping plane
5 nm p+Si/Si _{0.5} Ge _{0.5} DG-SL 5 periods
100 nm p+Si
p+ Si substrate

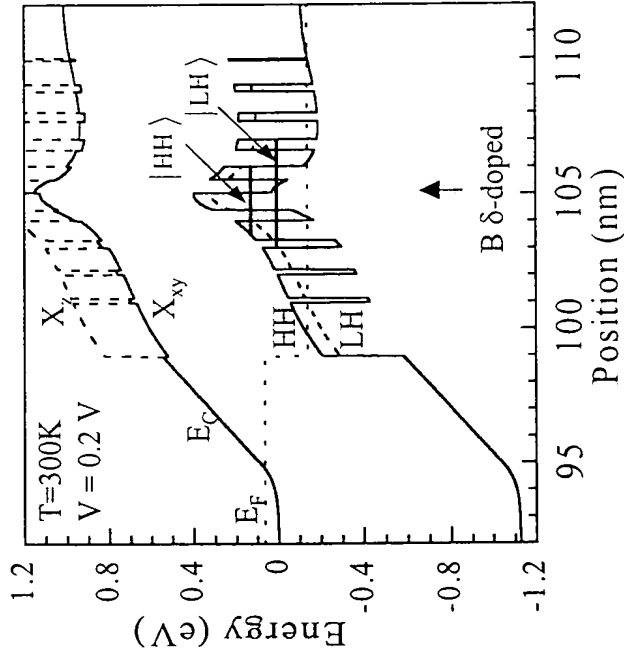


Figure 4

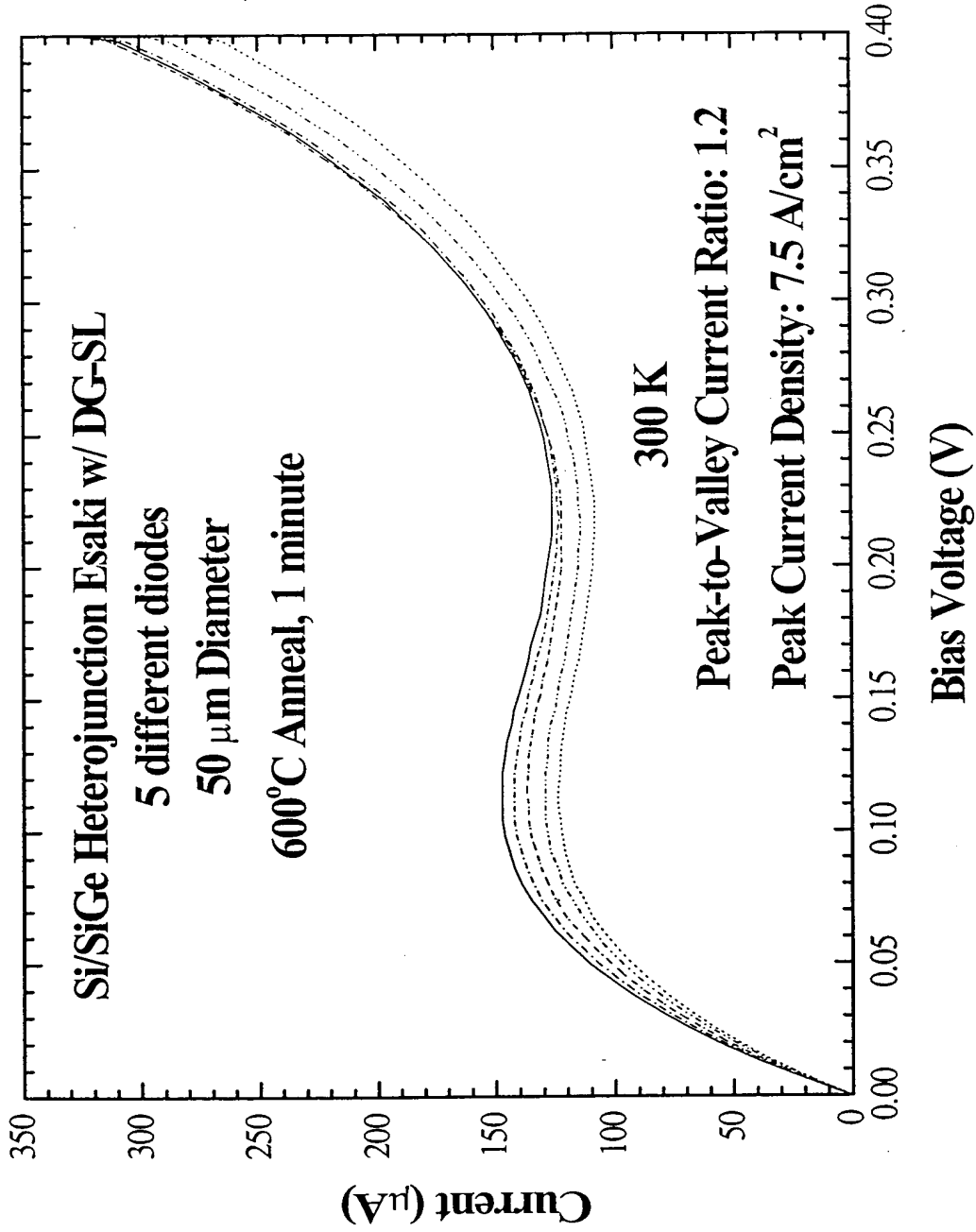


Figure 5

100 nm n+ Si	100 nm n+ Si
Sb-delta doping plane	Sb-delta doping plane
1 nm undoped Si	1 nm undoped Si
4 nm undoped Si _{0.5} Ge _{0.5}	4 nm undoped Si _{0.5} Ge _{0.5}
1 nm undoped Si	1 nm undoped Si
B-delta doping plane	B-delta doping plane
100 nm p+Si	100 nm p+Si
p+ Si substrate	p+ Si substrate

TD1

TD2

(a)

(b)

Figure 6

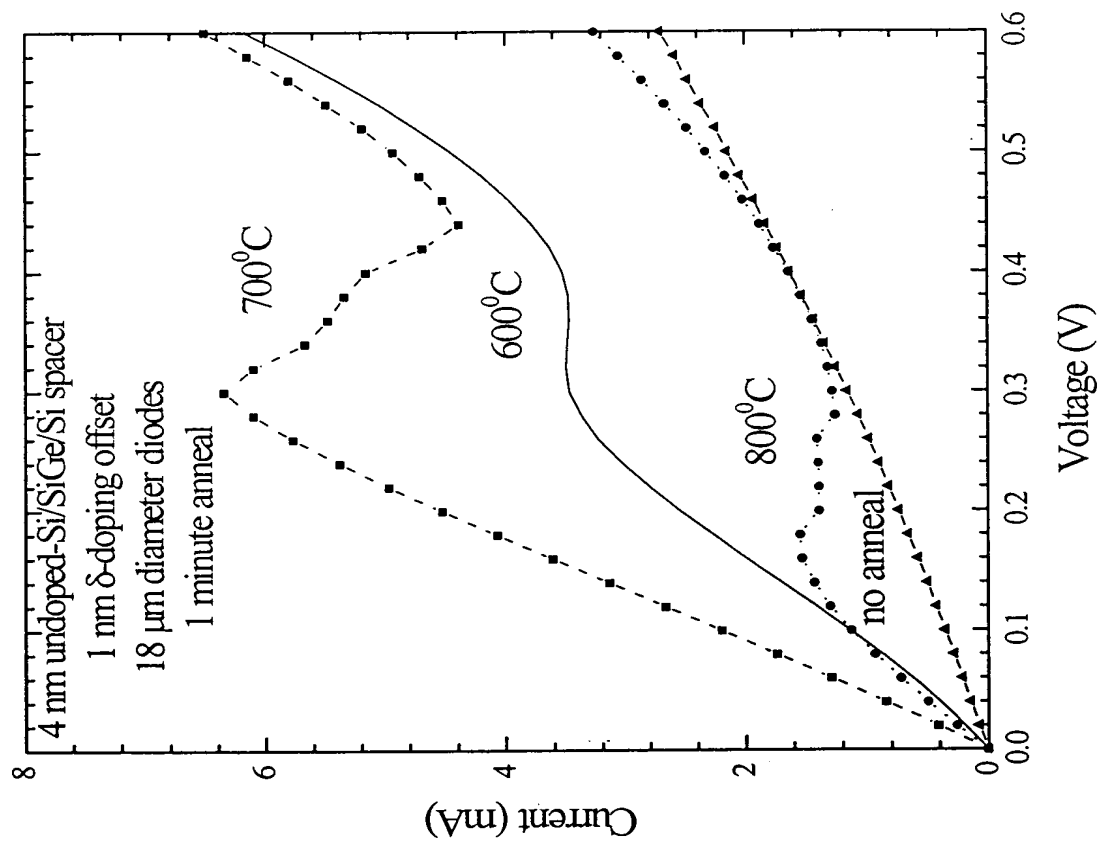
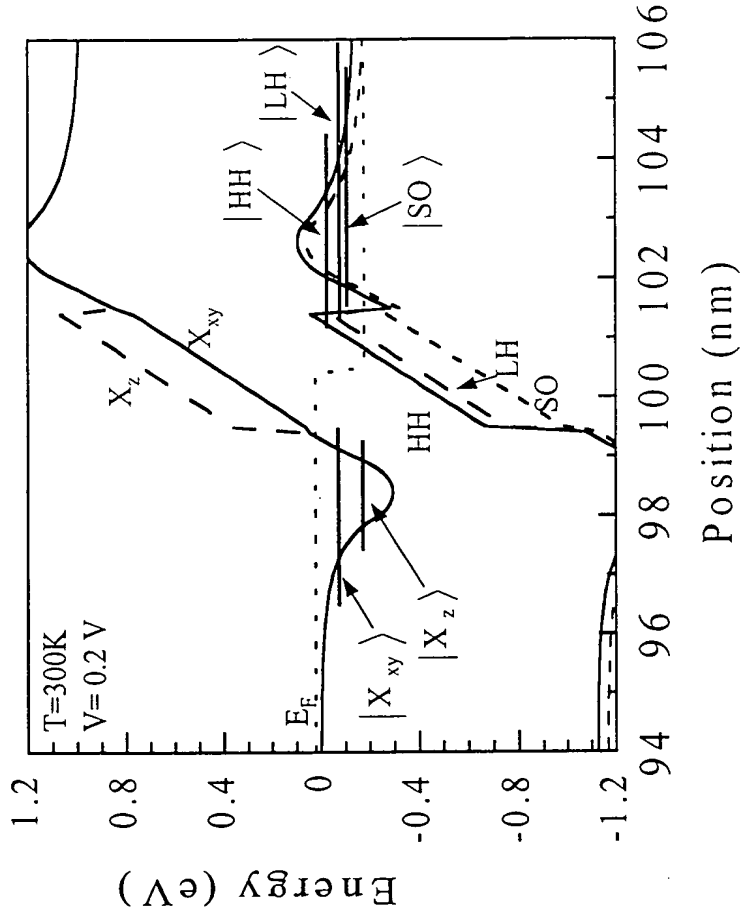


Figure 7

100 nm n+ Si
Sb δ -doping plane
1 nm undoped Si
2 nm undoped Si _{0.5} Ge _{0.5}
1 nm undoped Si
B δ -doping plane
100 nm p+Si
p+ Si substrate

TD3

(a)



(b)

Figure 8

FOF280" 4E3HE660

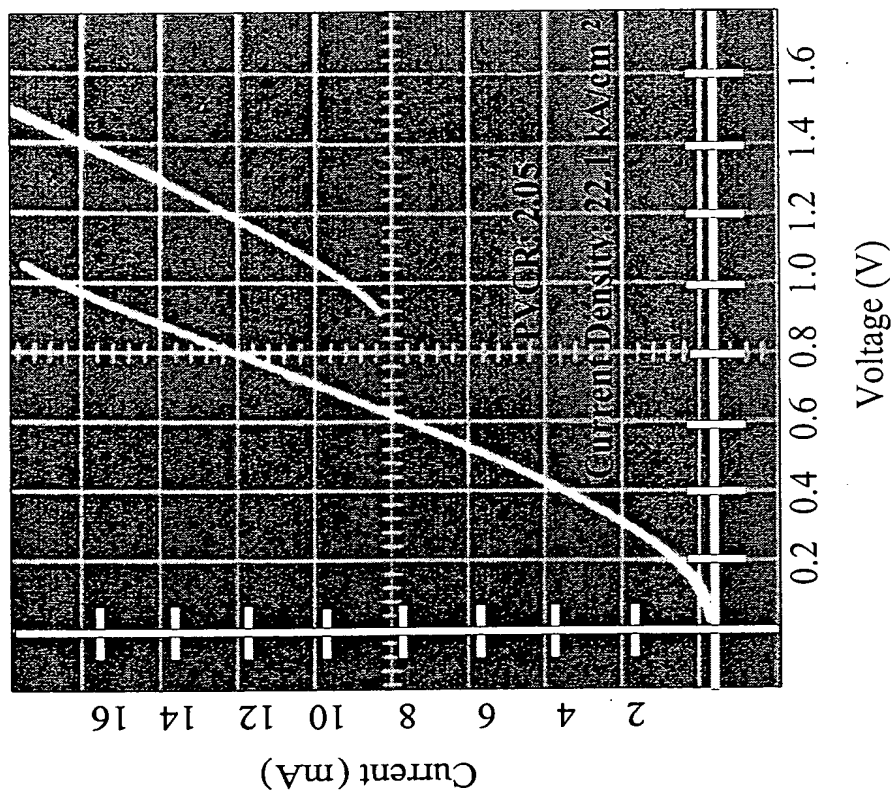


Figure 9